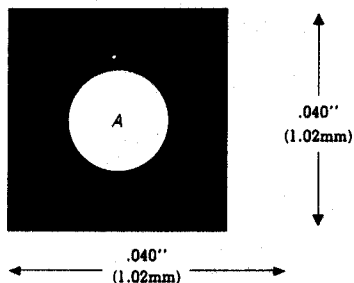


CHIP NUMBER

500



Anode: .020" (0.51mm) dia.

PN EPITAXIAL PLANAR POWER DIODE

CONTACT METALLIZATION

Anode: > 30,000 Å Aluminum

Cathode: Gold

(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL

Size: .140" Diameter (3.56mm)

Thickness: .010" (0.25mm)

ASSEMBLY RECOMMENDATIONS

It is advisable that:

a) the chip be eutectically mounted with gold silicon preform 98/2%.

b) 8 mil (0.203mm) aluminum wire be ultrasonically attached to the anode contact.

TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 500 in a DO-4 or equivalent case:

Minimum V_R @ 10 μA	I_R @ 80% V_R	V_F @	I_F	I_F Surge	Maximum t_{rr} @ $I_F = I_R = 1.0A$ $I_{REC} = 0.25A$
> 50V	< 5 μA	1.2V	1.5A	> 100A	200 ns
> 100V	< 5 μA	1.2V	1.5A	> 100A	200 ns
> 200V	< 5 μA	1.2V	1.5A	> 100A	200 ns
> 300V	< 5 μA	1.2V	1.5A	> 100A	200 ns
> 400V	< 5 μA	1.2V	1.5A	> 100A	450 ns
> 500V	< 5 μA	1.2V	1.5A	> 100A	450 ns

TYPICAL DEVICE TYPES: 1N5614, 1N5615, 1N5616

I_F surge $\geq 60A$.